DOCUMENT CHANGE REQUEST

DCR number 929

Changes required for: Qualification

Originator: Samuel Savin

Date: 2015/06/03

Date sent: 2015/04/21

Organisation: STMicroelectronics

Status: IMPLEMENTED

Title:	TRANSISTORS, POWER, MOSFET, P-CHANNEL, RAD-HARD BASED ON TYPE STRH12P10		
Number:	5205/029	Issue:	1

Other documents affected:

Page:

11

Paragraph:

2.5.2 High and Low Temperatures Electrical Measurements

Original wording:

0.95

Proposed wording:

1.25

Justification:

ST confirms that he didn't manufactured and sold any products since this spec was first published in December 2013. ST would like to reuse variants 01 & 02 for the new lots (re-centered the VGS(th) parameter in order to guarantee the TID performances).
The new lot with re-centering VGS(th) parameter has impacted the VSD parameter. These parameter is increasing about 25%.
ST would like change the maximum limit at high temperature on VSD parameter with 1.25V instead of 0.95V

Attachments:
strh12p10_dcr.pdf
Modifications:
N/A
Approval signature:
Date signed:
2015-06-03